



One-cell Li-ion/Li-polymer battery protection IC

# MD1421ExxCPAL series

#### Outline

MD1421ExxCPAL series are protection IC with integrated MOSFET for protection of the rechargeable lithium-ion or lithiumpolymer battery. The overcharge, overdischarge and discharging and charging overcurrent protection of the rechargeable one-cell lithium-ion or lithium-polymer battery can be detected.

#### Features

1) Range and accuracy of detection/release voltage

- Overcharge detection voltage
- Overcharge release voltage
- Overdischarge detection voltage
- Overdischarge release voltage
- Discharging overcurrent detection voltage
- Charging overcurrent detection voltage
- Short detection voltage
- $\cdot\,$  Over voltage charger detection voltage
- $\cdot$  Over voltage charger release voltage

(Unless otherwise specified,Ta=25℃)

4.1V to 4.45V, 5mV steps 3.9V to 4.3V %1 2.0V to 3.0V %2 2.0V to 3.2V %2 +40mV to +180mV, 5mV steps -180mV to -40mV, 5mV steps Selection from 0.56V, 0.9V VDD-8.0V fixed VDD-7.3V fixed

- Accuracy±20mV Accuracy±50mV Accuracy±100mV Accuracy±100mV Accuracy±5mV Accuracy±15mV Accuracy±100mV Accuracy±2.0V Accuracy±2.0V
- \*1 Hysteresis voltagebetween Overcharge detection and release voltage is selectable from 0.10V/0.15V/0.20V/0.25V.
- \*2 Please inquire to us about details of the setting of Overdischarge detection and release voltage.

#### 2) Range of detection delay time

<ul> <li>Overcharge detection delay time</li> </ul>	Selection from 1.0s, 4.5s, 6.25s
<ul> <li>Overdischarge detection delay time</li> </ul>	Selection from 100ms, 256ms
<ul> <li>Discharging overcurrent detection delay time</li> </ul>	Selection from 8ms, 12ms, 16ms, 20ms, 34ms
<ul> <li>Charging overcurrent detection delay time</li> </ul>	Selection from 8.5ms, 25ms, 32.5ms
<ul> <li>Short detection delay time</li> </ul>	Selection from 0.50ms, 0.75ms, 1.00ms
3) 0V battery charge function	Selection from "Prohibition" or "Permission"

4) The overcharge detection delay timer reset time function (function for the pulse charge) is provided.

5) Low current consumption

・Normal mode	Typ. 3.0uA,	Max. 5.2uA
<ul> <li>Stand-by mode</li> </ul>	Max. 0.1uA	(For "Charger connection release" the overdischarge release condition.)
	Max. 0.5uA	(For "Voltage release" the overdischarge release condition.)

6) MOS-FET

Source to Source on state resistance

Typ. 38.0m $\Omega$  ( <code>@VCC=3.7V</code>)

MinebeaMitsumi		Mitsumi Q Search	Mitsumi Electric CO.,LTD.			
Passion to Create Value through Difference		https://mtm-sec.mitsumi.co.jp/web/ic/	Semiconductor Business Division Strategy Engineering Department   tel:+81-46-230-3470			
All brand names, logos, product names, trade names and service names described here are trademarks or registered trademarks of their respective companies or organizations.						
Any products mentioned in this leaflet are subject to any modification in their appearance and others for improvements without prior notification.						
The details listed here are not a guarantee of the individual products at the time of ordering. When using the products, you will be asked to check their specifications.						





7) Package type

• PLP-4-1228

2.85 × 1.25 × 0.60 [mm]

**Pin explanations** 

PLP-4-1228	Pin No.	Symbol	l Function		
	1	S1	Negative power supply and source of discharge MOS-FET terminal. Connect to the negative terminal of the battery.		
2 VCC Positive power supply voltage input terminal. Connect to the positive terminal of the battery t		Positive power supply voltage input terminal. Connect to the positive terminal of the battery through R1.			
1 D 4 2 - D 3	3	IDT	Charger negative voltage input terminal. Connect to S2 terminal through R2.		
	4	S2	Source terminal of charge MOS-FET. Connect to a negative power supply terminal of charger.		
	-	D	Drain terminal of discharge and charge MOS-FET. Drain terminal must be open electrically.		



## Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit
Supply voltage	VCC	-0.3	12	V
Pin voltage	VIDT	VCC-24	VCC+0.3	V
Drain-source voltage	VDSS	-	24	V
Drain current	ID	-	6.0	А
Storage temperature	TSTG	-40	125	C

### **Recommended Operating Conditions**

Parameter	Symbol	Min	Max	Unit
Operating ambient temperature	TOPE	-40	85	°
Operating voltage	VCCop1	1.5	5.5	V

## Electrical characteristics

(Unless otherwise specified,Ta=25℃)							
Parameter	Symbol	Note	Min	Тур	Max	Unit	
Current consumption							
Current consumption	Icc1	VCC=3.6V, IDT=0V	-	3.0	5.2	uA	
Current concumption at stand by	Icc2	Vdet2 = Vrel2	-	-	0.1	uA	
Current consumption at stand-by	Icc3	Vdet2≠Vrel2	-	-	0.5	uA	
		Detection/Release voltage	ge				
Overcharge detection voltage	V1		Тур-0.020	V1	Typ+0.020	V	
Overcharge release voltage	V2		Typ-0.050	V2	Typ+0.050	V	
Overdischarge release voltage	V3		Тур-0.100	V3	Typ+0.100	V	
Overdischarge detection voltage	V4		Тур-0.100	V4	Typ+0.100	V	
Discharge Overcurrent detection voltage 1	V5_1	VCC=4.5V	Тур-0.008	V5_1	Typ+0.008	V	
Discharge Overcurrent detection voltage 2	V5_2	VCC=3.5V	Typ-0.005	V5_2	Typ+0.005	V	
Discharge Overcurrent detection voltage 3	V5_3	VCC=2.5V	Тур-0.008	V5_3	Typ+0.008	V	
Short detection voltage	V6		Тур-0.100	V6	Typ+0.100	V	
			0.40	0.65	1.10	V	
ov battery charge inhibition battery voltage	V /		0.65	0.90	1.25	V	
Overvoltage charger detection voltage	V8det		6.0	8.0	10.0	V	
Overvoltage charger release voltage	V8rec		5.8	7.3	8.8	V	
Charge Overcurrent detection voltage	V9		Typ-0.015	V9	Typ+0.015	V	
		Detection delay time					
Overdischarge detection delay time	Tsp1		Typ*0.75	Tsp1	Typ*1.25	ms	
Discharging overcurrent detection delay time	Tsp2		Typ*0.75	Tsp2	Typ*1.25	ms	
Overcharge detection delay time	Tsp3		Typ*0.75	Tsp3	Typ*1.25	S	
Short detection delay time	Tsp4		Typ*0.75	Tsp4	Typ*1.25	us	
Charging overcurrent detection delay time	Tsp5		Typ*0.75	Tsp5	Typ*1.25	ms	
MOS-FET							
Drain current of cut off	IDSS	VDS=24V	-	-	1.0	uA	
Source to source on state resistance 1	RSS(on)1	VCC=4.5V , Is=1.0A	27.0	36.0	45.0	mΩ	
Source to source on state resistance 2	RSS(on)2	VCC=3.5V , Is=1.0A	30.0	39.0	48.0	mΩ	
Source to source on state resistance 3	RSS(on)3	VCC=2.5V , Is=1.0A	33.0	48.0	65.0	mΩ	
Body diode forward voltage	VSD	Is=1A	0.50	0.70	1.00	V	





Block diagram / Typical application circuit



Symbol	Part	Min.	Тур.	Max.	Unit
Rvcc	Resistor	-	33	470	Ω
C1/C2/C3	Capacitor	0.01	0.1	1.0	uF
Ridt	Resistor	_	2.7k	_	Ω

% Application hints

The resistors that are inserted into each pin are to protect the IC. They help to remove ESD and latch-up damages. The capacitors help to reduce the effects of transient variations in voltage and electromagnetic waves, and to improve ESD tolerance of the IC.Please use either C2 or C3, or both of them by request of your application.

These values in the above figure are for example. Please choose appropriate values.